

# FDBL0120N40

## May 2024

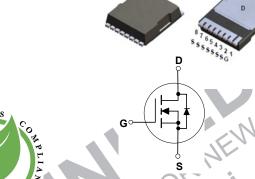
# N-Channel PowerTrench® MOSFET **40 V, 240 A, 1.2 m**Ω

## **Features**

- Typical  $R_{DS(on)}$  = 0.9 m $\Omega$  at  $V_{GS}$  = 10V,  $I_D$  = 80 A
- Typical  $Q_{q(tot)}$  = 90 nC at  $V_{GS}$  = 10V,  $I_D$  = 80 A
- UIS Capability
- RoHS Compliant

## **Applications**

- Industrial Motor Drive
- Industrial Power Supply
- Industrial Automation
- Battery Operated tools
- Battery Protection
- Solar Inverters
- UPS and Energy Inverters
- Energy Storage
- Load Switch



For current package drawing, please refer to the Fairchild website at https://www.fairchildsemi.com/evaluate/package-specifications/packageDetails.html?id=PN\_PSOFA-008

## **MOSFET Maximum Ratings** T<sub>J</sub> = 25°C unless otherwise noted.

Symbol	Parameter	Ratings	Units
$V_{DSS}$	Drain-to-Source Voltage	40	V
$V_{GS}$	Gate-to-Source Voltage	±20	V
	Drain Current - Continuous ( $V_{GS}$ =10) (Note 1) $T_C$ = 25°C	240	А
ID	Pulsed Drain Current T <sub>C</sub> = 25°C	See Figure 4	_ A
E <sub>AS</sub>	Single Pulse Avalanche Energy (Note 2)	316	mJ
D	Power Dissipation	300	W
$P_{D}$	Derate Above 25°C	2.0	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature	-55 to + 175	°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.5	°C/W
$R_{\theta JA}$	Maximum Thermal Resistance, Junction to Ambient (Note 3)	43	°C/W

## Notes:

- Current is limited by bondwire configuration.
   Starting T<sub>J</sub> = 25°C, L = 0.1mH, I<sub>AS</sub> = 79.5A, V<sub>DD</sub> = 40V during inductor charging and V<sub>DD</sub> = 0V during time in avalanche.
   R<sub>θ,JA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>θ,JC</sub> is guaranteed by design, while R<sub>θ,JA</sub> is determined by the board design. The maximum rating presented here is based on mounting on a 1 in<sup>2</sup> pad of 2oz copper.

## **Package Marking and Ordering Information**

Device Marking	Device	Package			
FDBL0120N40	FDBL0120N40	MO-299A	-	-	-

Units

Max.

# **Electrical Characteristics** $T_J = 25^{\circ}C$ unless otherwise noted.

**Parameter** 

Off Characteristics							
B <sub>VDSS</sub>	Drain-to-Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$		40	-	-	V
I <sub>DSS</sub>	Drain-to-Source Leakage Current	V <sub>DS</sub> =40V,	$T_{\rm J} = 25^{\rm o}{\rm C}$	-	-	1	μΑ
		$V_{GS} = 0V$	$T_J = 175^{\circ}C \text{ (Note 4)}$	-	-	1	mA
I <sub>GSS</sub>	Gate-to-Source Leakage Current	$V_{GS} = \pm 20V$		-	-	±100	nA

**Test Conditions** 

Min.

Тур.

## **On Characteristics**

Symbol

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$		2.0	3.2	4.0	V
R <sub>DS(on)</sub> Drain to Source On	Drain to Course On Registance	I <sub>D</sub> = 80A,	$T_{\rm J} = 25^{\rm o}{\rm C}$	-	0.90	1.20	$m\Omega$
	Diam to Source On Resistance	V <sub>GS</sub> = 10V	$T_J = 175^{\circ}C \text{ (Note 4)}$	-,	1.64	1.86	mΩ

## **Dynamic Characteristics**

					1
C <sub>iss</sub>	Input Capacitance	V - 25V V - 2V	- 7735	VI- N	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1MHz	- 2160	1 -	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	T = TIVITIZ	- 129	-	pF
$R_g$	Gate Resistance	f = 1MHz	2.5	-	Ω
$Q_{g(ToT)}$	Total Gate Charge at 10V	$V_{GS} = 0 \text{ to } 10V$ $V_{DD} = 32V$	90	107	nC
$Q_{g(th)}$	Threshold Gate Charge	$V_{GS} = 0 \text{ to } 2V$ $I_D = 80A$	- 13.5	15.5	nC
$Q_{gs}$	Gate-to-Source Gate Charge	OFF	- 43	\ \ '-	nC
$Q_{gd}$	Gate-to-Drain "Miller" Charge	D. NV.B	- 10	-	nC

# **Switching Characteristics**

t <sub>on</sub>	Turn-On Time	-	-	102	ns
t <sub>d(on)</sub>	Turn-On Delay	-	33	1	ns
t <sub>r</sub>	Rise Time $V_{DD} = 20V$ , $I_D = 80A$ ,	-	40	1	ns
t <sub>d(off)</sub>	Turn-Off Delay $V_{GS} = 10V, R_{GEN} = 6\Omega$	-	47	-	ns
t <sub>f</sub>	Fall Time	-	23	-	ns
t <sub>off</sub>	Turn-Off Time	-	-	91	ns

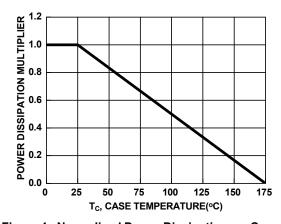
# **Drain-Source Diode Characteristics**

V	Source-to-Drain Diode Voltage	$I_{SD}$ =80A, $V_{GS}$ = 0V		-	1.25	٧
V <sub>SD</sub> Source-to-Drain Diode Voltage	$I_{SD}$ = 40A, $V_{GS}$ = 0V		-	1.2	V	
t <sub>rr</sub>	Reverse-Recovery Time	$I_F = 80A$ , $dI_{SD}/dt = 100A/\mu s$ ,		91	107	ns
Q <sub>rr</sub>	Reverse-Recovery Charge	V <sub>DD</sub> =32V	-	128	167	nC

## Note:

4: The maximum value is specified by design at  $T_J = 175$  °C. Product is not tested to this condition in production.

# **Typical Characteristics**



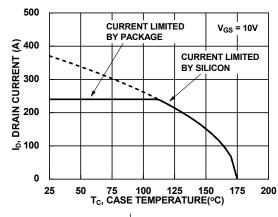
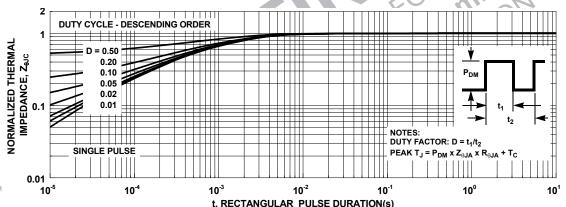


Figure 1. Normalized Power Dissipation vs. Case Temperature

Figure 2. Maximum Continuous Drain Current vs.

Case Temperature



t, RECTANGULAR PULSE DURATION(s)
Figure 3. Normalized Maximum Transient Thermal Impedance

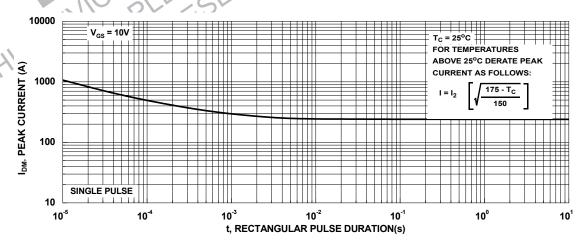


Figure 4. Peak Current Capability

# **Typical Characteristics**

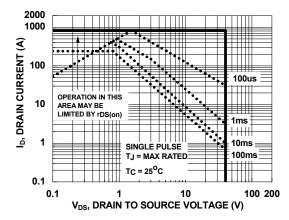
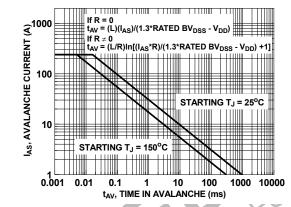


Figure 5. Forward Bias Safe Operating Area



NOTE: Refer to Fairchild Application Notes AN7514 and AN7515

Figure 6. Unclamped Inductive Switching

Capability

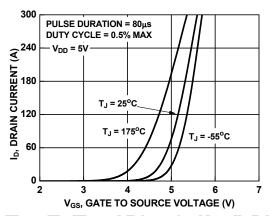


Figure 7. Transfer Characteristics

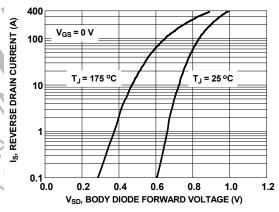


Figure 8. Forward Diode Characteristics

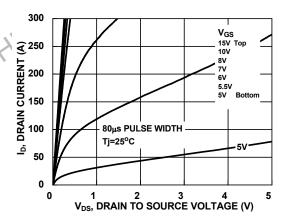


Figure 9. Saturation Characteristics

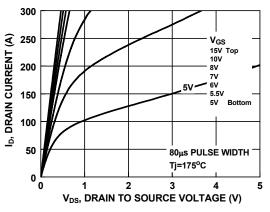


Figure 10. Saturation Characteristics

# **Typical Characteristics**

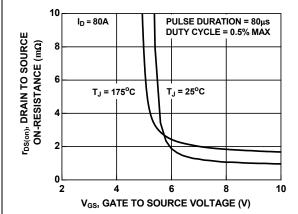


Figure 11. R<sub>DSON</sub> vs. Gate Voltage

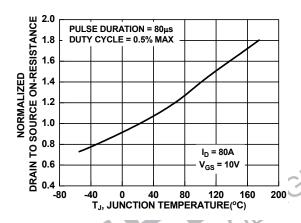


Figure 12. Normalized R<sub>DSON</sub> vs. Junction Temperature

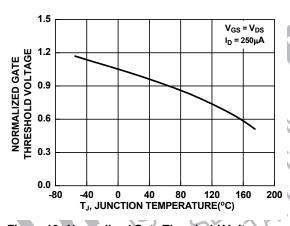


Figure 13. Normalized Gate Threshold Voltage vs. Temperature

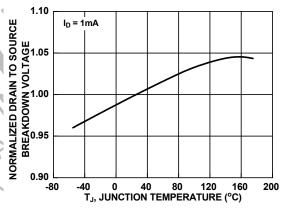


Figure 14. Normalized Drain to Source Breakdown Voltage vs. Junction Temperature

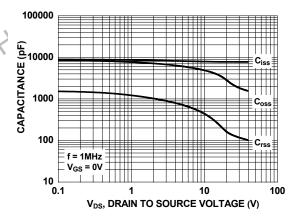


Figure 15. Capacitance vs. Drain to Source Voltage

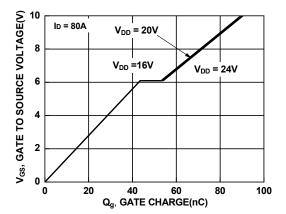


Figure 16. Gate Charge vs. Gate to Source Voltage





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